

2SD1862
Rev.E Mar.-2016

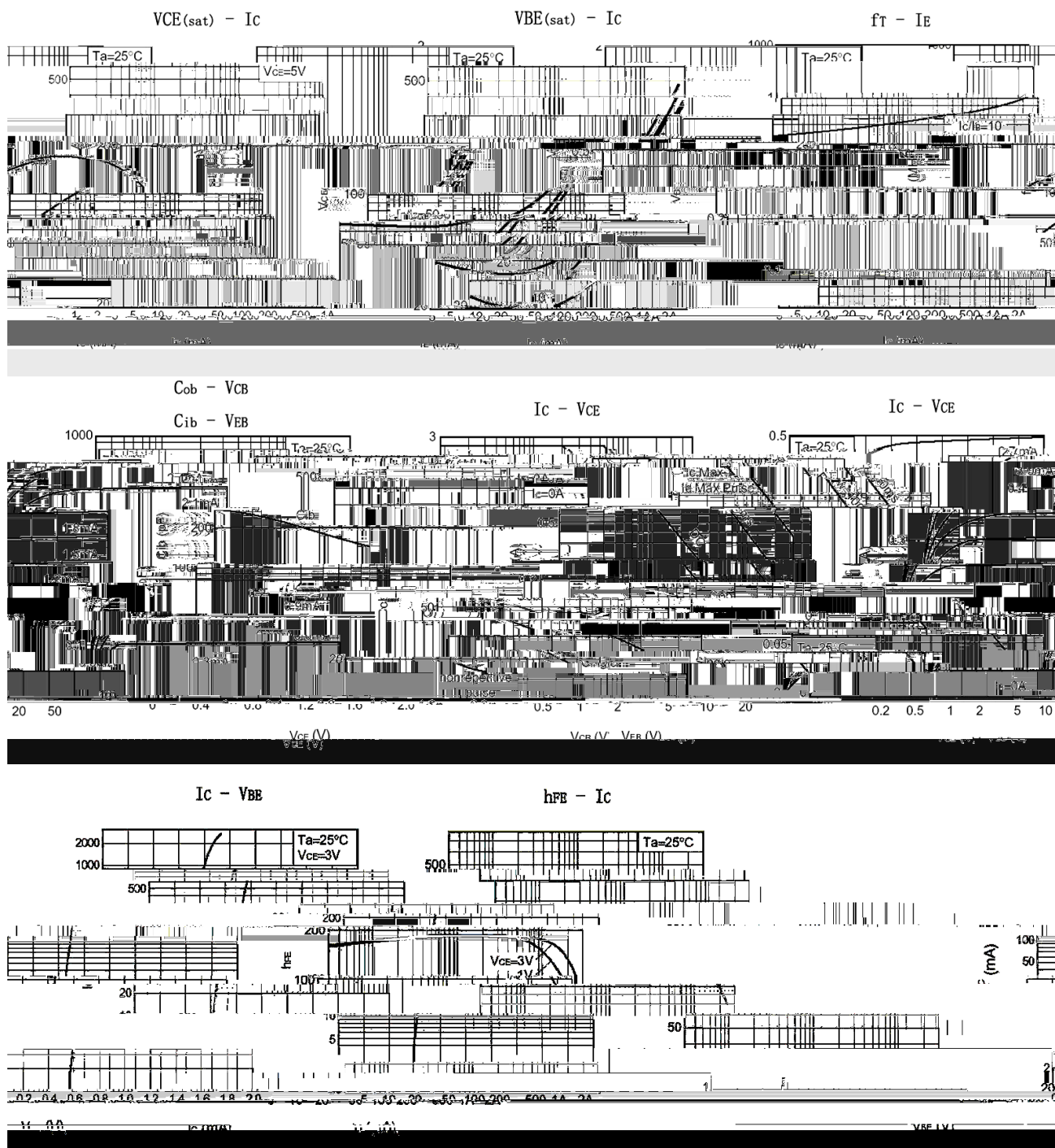
TO-92LM NPN Silicon NPN transistor in a TO-92LM Plastic Package.

Low V_{CE} , 2SB1240

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	32	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	2.0	A
Collector Current (Pulse)	I_{CP}	2.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50\mu A$ $I_B=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	32			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=50\mu A$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=20V$ $I_E=0$			1.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4.0V$ $I_C=0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=3.0V$ $I_C=0.5A$	120		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.0A$ $I_B=0.2A$		0.5	0.8	V
Transition Frequency	f_T	$V_{CE}=5.0V$ $f=100MHz$ $I_C=50mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V$ $f=1.0MHz$ $I_E=0$		30		pF

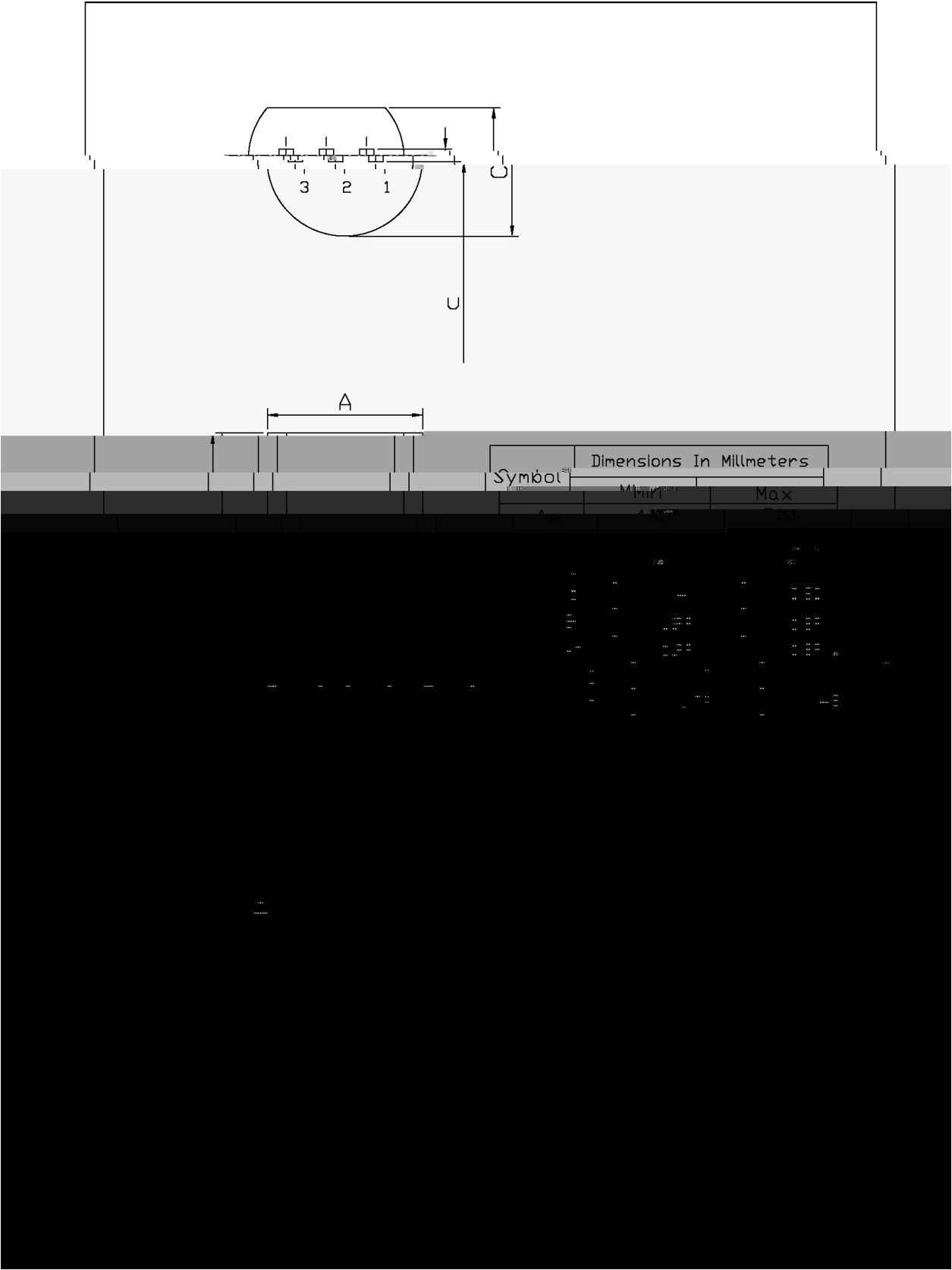
/ Electrical Characteristic Curve

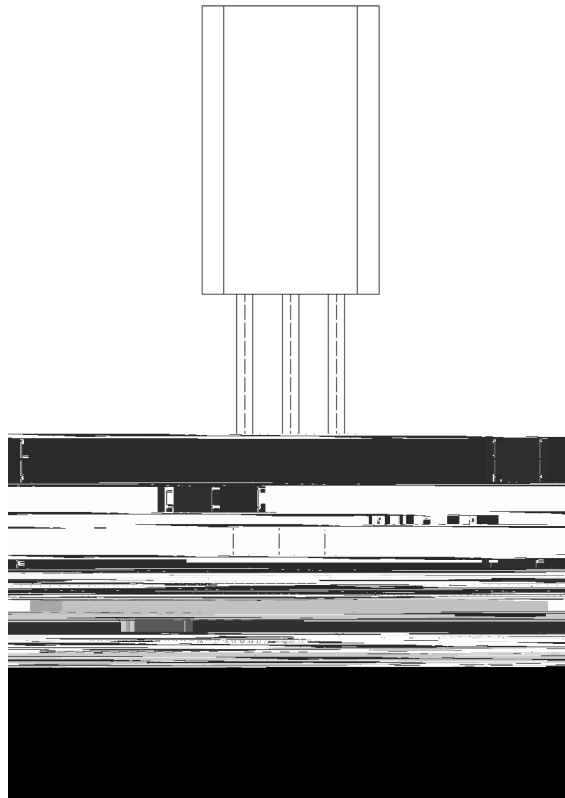


/ PackageDimensions

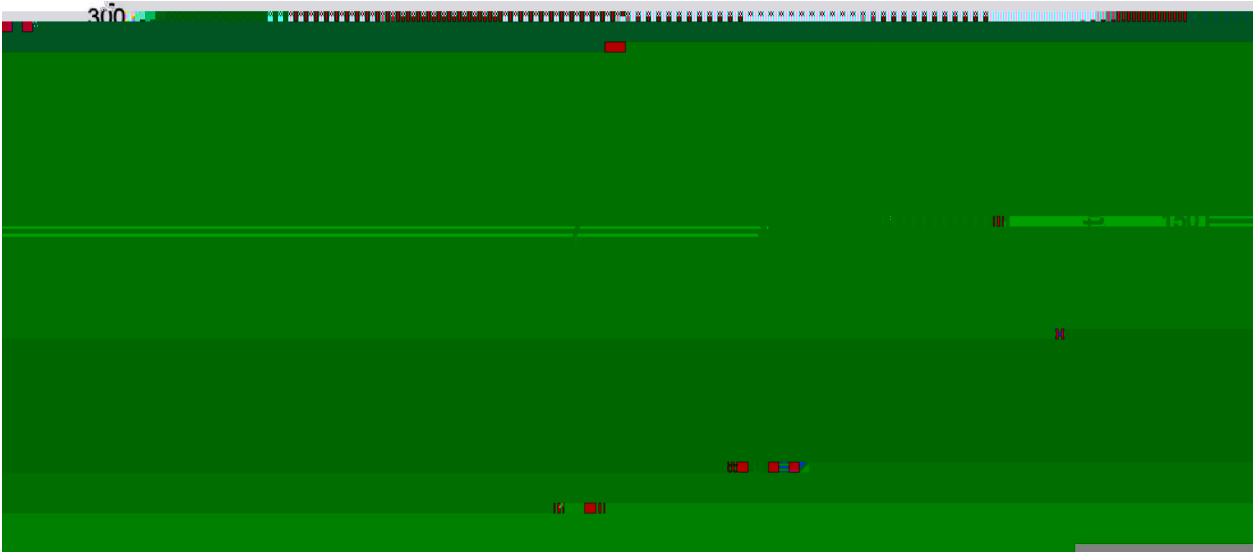
T0-92LM

Unit: mm





() / Temperature Profile for Dip Soldering(Pb-Free)



- Note:

1	25	150	60	90sec;	1.Preheating:25~150℃ , Time:60~90sec.
2	255±5		5±0.5sec;	2.Peak Temp.:255±5℃ , Duration:5±0.5sec.	
3		2	10℃/sec.	3. Cooling Speed: 2~10℃/sec.	

270±5 10±1 sec. Temp.:270±5